

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8674 — General-Purpose Switching Device Applications

Features

- 1.8V drive
- · Composite type, facilitating high-density mounting
- · Halogen free compliance
- · Protection diode in

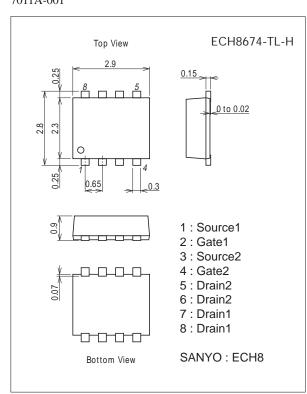
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-30	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm) 1unit	1.3	W
Total Power Dissipation	PT	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-001

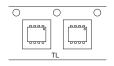


Product & Package Information

Package : ECH8JEITA, JEDEC : -

• Minimum Packing Quantity : 3,000 pcs./reel

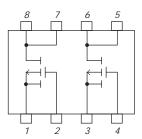
Packing Type: TL



Marking



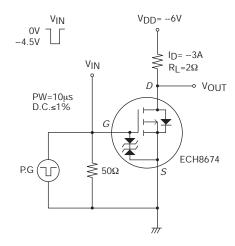
Electrical Connection



Electrical Characteristics at Ta=25°C

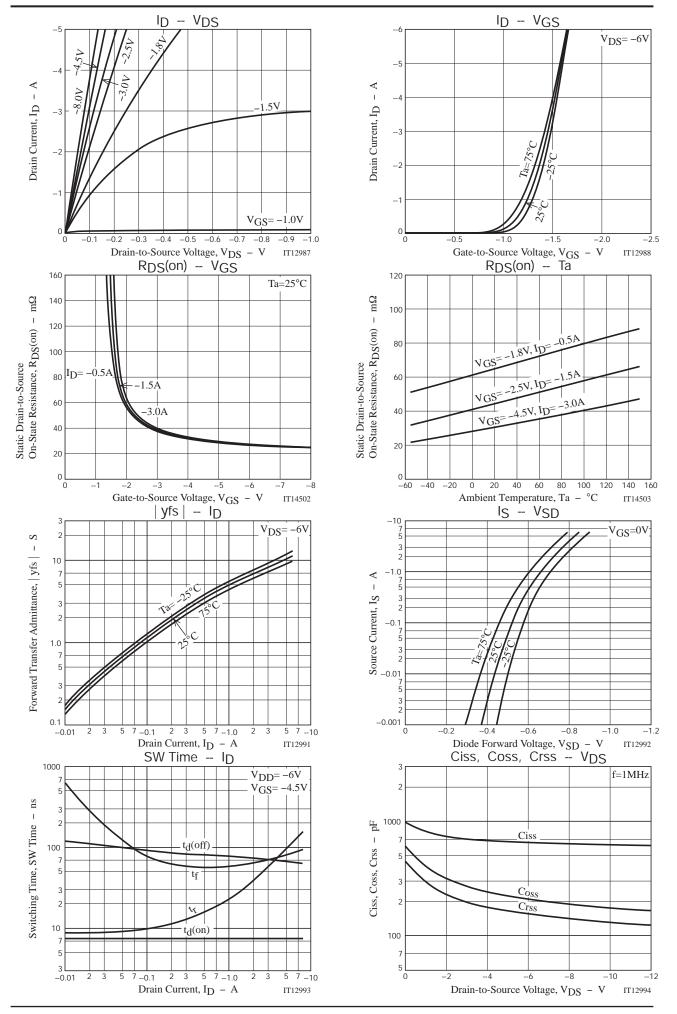
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	I _{DSS} 1	V _{DS} =-8V, V _{GS} =0V			-1	μΑ	
	I _{DSS} 2	V _{DS} =-12V, V _{GS} =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _D S=-6V, I _D =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =-6V, I _D =-3A	4.8	8.1		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-3A, V _G S=-4.5V		31	41	mΩ	
	R _{DS} (on)2	I _D =-1.5A, V _G S=-2.5V		45	63	mΩ	
	RDS(on)3	ID=-0.5A, VGS=-1.8V		66	95	mΩ	
Input Capacitance	Ciss			660		pF	
Output Capacitance	Coss	V _{DS} =-6V, f=1MHz		210		pF	
Reverse Transfer Capacitance	Crss	_		155		pF	
Turn-ON Delay Time	t _d (on)			7.4		ns	
Rise Time	tr	Constitution Total Circuit		57		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		72		ns	
Fall Time	tf			69		ns	
Total Gate Charge	Qg			6.9		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-5A		1.2		nC	
Gate-to-Drain "Miller" Charge	Qgd	_		1.8		nC	
Diode Forward Voltage	V _{SD}	I _S =-5A, V _{GS} =0V		-0.83	-1.2	V	

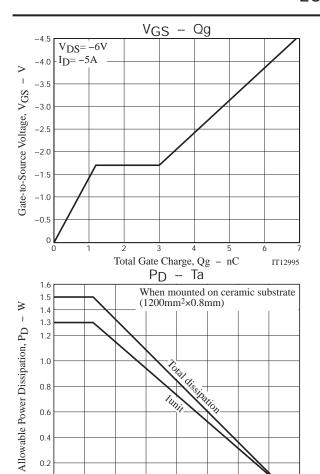
Switching Time Test Circuit



Ordering Information

Device	Device Package		memo	
ECH8674-TL-H	CH8674-TL-H ECH8		Pb Free and Halogen Free	

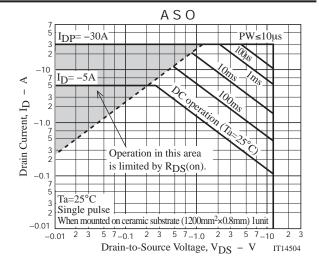




40 60 80 100 120 Ambient Temperature, Ta - °C 10 160 IT14505

0 L

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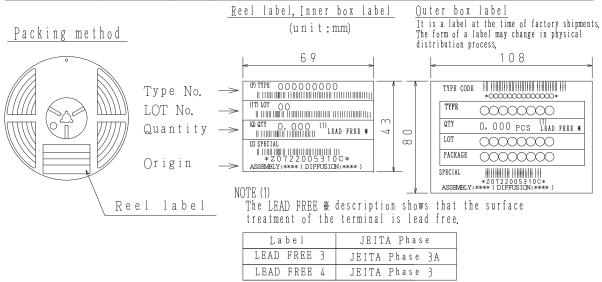


Embossed Taping Specification

ECH8674-TL-H

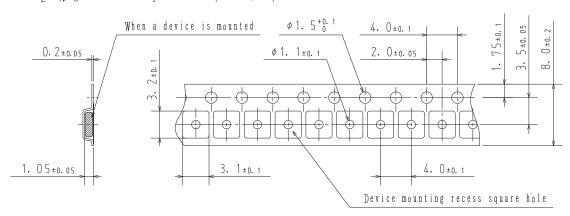
1. Packing Format

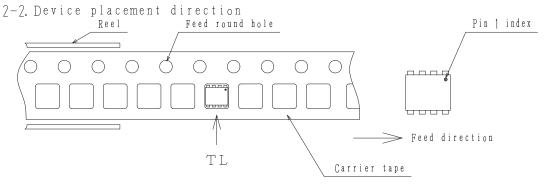
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)

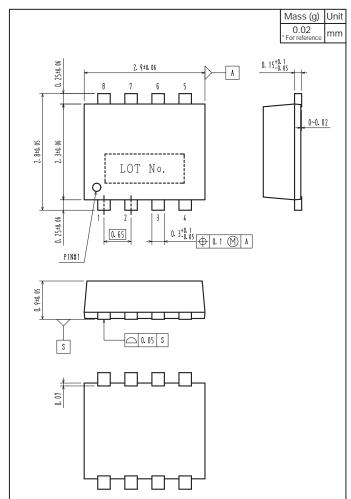




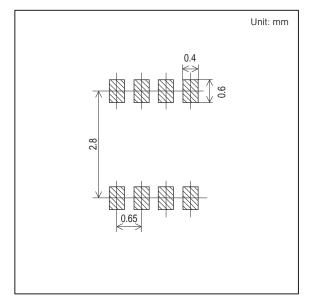
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8674-TL-H



Land Pattern Example



Note on usage: Since the ECH8674 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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